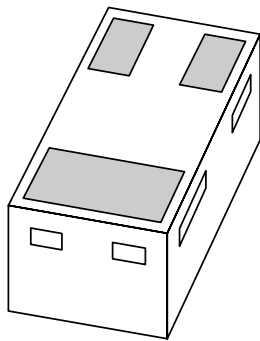


DATA SHEET



PESDxL2UM series Low capacitance double ESD protection diode

Product data sheet
Supersedes data of 2003 Aug 05

2005 May 23

Low capacitance double ESD protection diode

PESDxL2UM series

FEATURES

- Uni-directional ESD protection of two lines or bi-directional ESD protection of one line
- Reverse standoff voltage 3.3 and 5 V
- Low diode capacitance
- Ultra low leakage current
- Leadless ultra small SOT883 surface mount package (1 × 0.6 × 0.5 mm)
- Board space 1.17 mm² (approx. 10% of SOT23)
- ESD protection >15 kV
- IEC 61000-4-2; level 4 (ESD); 15 kV (air) or 8 kV (contact).

APPLICATIONS

- Cellular handsets and accessories
- Portable electronics
- Computers and peripherals
- Communication systems
- Audio and video equipment.

MARKING

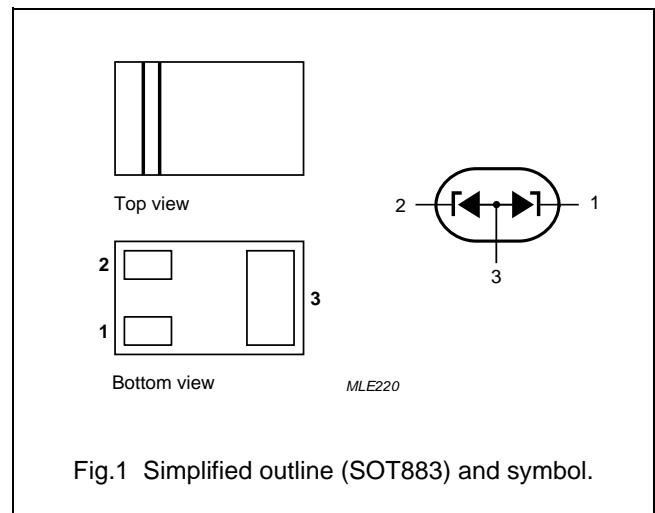
TYPE NUMBER	MARKING CODE
PESD3V3L2UM	F2
PESD5V0L2UM	F1

DESCRIPTION

Low capacitance ESD protection diode in a three pad SOT883 leadless ultra small plastic package designed to protect up to two transmission or data lines from ElectroStatic Discharge (ESD) damage.

PINNING

PIN	DESCRIPTION
1	cathode 1
2	cathode 2
3	common anode



Low capacitance double ESD protection diode

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
I _{pp}	peak pulse current	8/20 μs pulse; notes 1, 2 and 3	–	3	A
	PESD3V3L2UM PESD5V0L2UM			2.5	A
P _{pp}	peak pulse power	8/20 μs pulse; notes 1, 2 and 3	–	30	W
I _{FSM}	non-repetitive peak forward current	t _p = 1 ms; square pulse	–	3.5	A
I _{ZSM}	non-repetitive peak reverse current	t _p = 1 ms; square pulse	–	0.9	A
	PESD3V3L2UM PESD5V0L2UM			0.8	A
P _{tot}	total power dissipation	T _{amb} = 25 °C; note 4	–	250	mW
P _{ZSM}	non-repetitive peak reverse power dissipation	t _p = 1 ms; square pulse; see Fig.4	–	6	W
T _{stg}	storage temperature		–65	+150	°C
T _j	junction temperature		–	150	°C
ESD	electrostatic discharge	IEC 61000-4-2 (contact discharge)	15	–	kV
		HBM MIL-Std 883	10	–	kV

Notes

1. Non-repetitive current pulse 8/20 μs exponential decay waveform; see Fig.5.
2. Pins 1 and 3 or 2 and 3.
3. Pins 1 and 2.
4. Device mounted on standard printed-circuit board.

ESD standards compliance

IEC 61000-4-2, level 4 (ESD)	>15 kV (air); >8 kV (contact)
HBM MIL-Std 883, class 3	>4 kV

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	all diodes loaded; note 1	500	K/W
		one diode loaded; note 2	290	K/W

Notes

1. Refer to SOT883 standard mounting conditions (footprint), FR4 with 60 μm copper strip line.
2. FR4 single-sided copper 1 cm².

Low capacitance double ESD protection diode

PESDxL2UM series

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

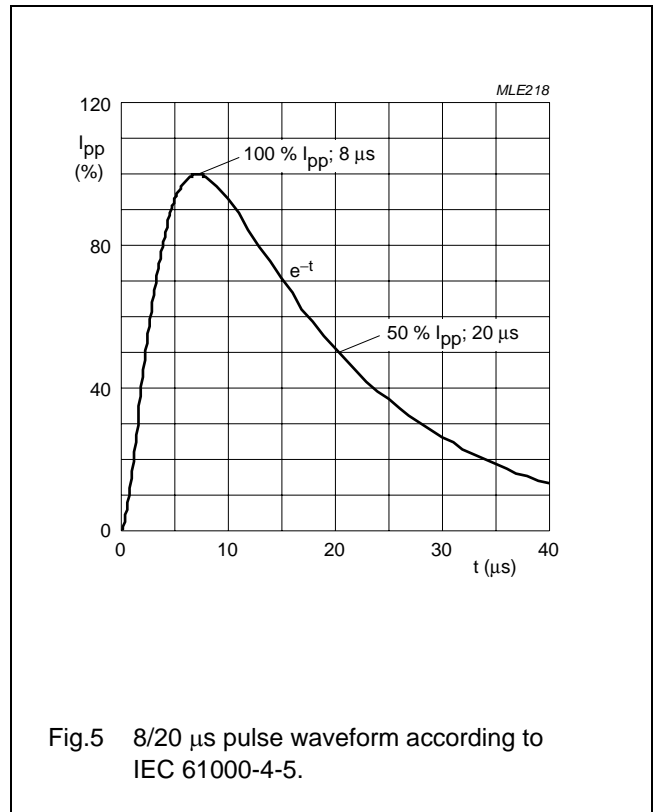
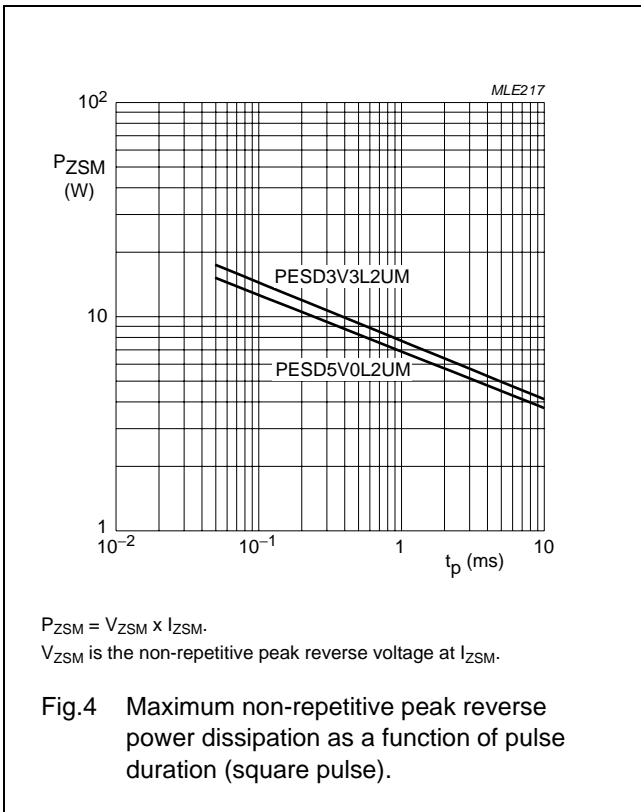
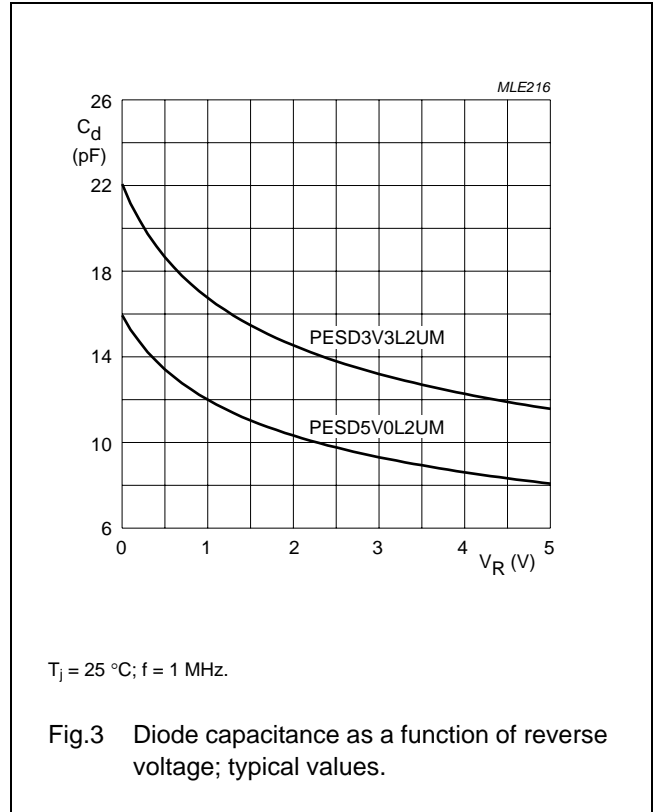
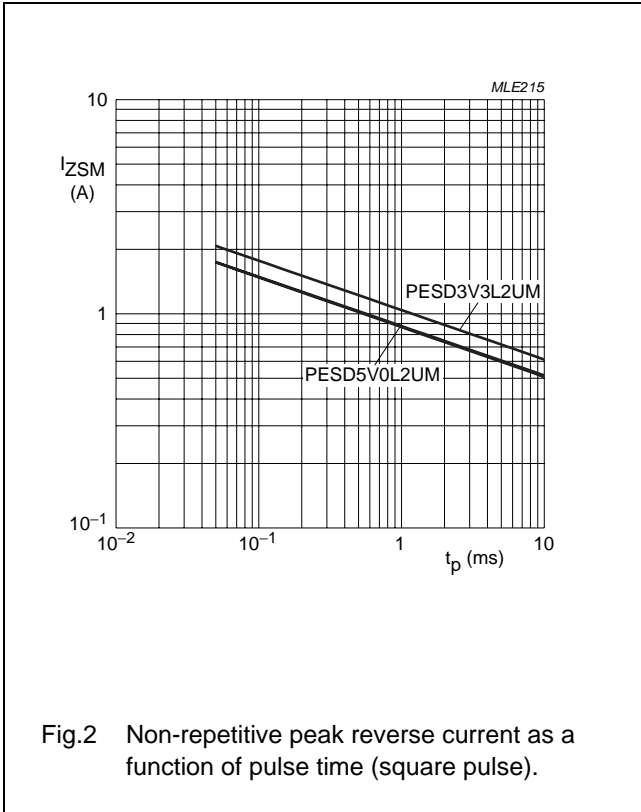
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V _F	forward voltage	I _F = 200 mA	–	1	1.2	V
V _{RWM}	reverse stand-off voltage					
	PESD3V3L2UM		–	–	3.3	V
	PESD5V0L2UM		–	–	5	V
I _{RM}	reverse leakage current					
	PESD3V3L2UM	V _R = 3.3 V	–	75	300	nA
	PESD5V0L2UM	V _R = 5 V	–	5	25	nA
V _{(CL)R}	clamping voltage PESD3V3L2UM	8/20 μs pulse				
		I _{pp} = 1 A; notes 1 and 2	–	–	8	V
		I _{pp} = 3 A; notes 1 and 2	–	–	12	V
		I _{pp} = 1 A; notes 1 and 3	–	–	9	V
	PESD5V0L2UM	I _{pp} = 3 A; notes 1 and 3	–	–	13	V
		I _{pp} = 1 A; notes 1 and 2	–	–	10	V
		I _{pp} = 2.5 A; notes 1 and 2	–	–	13	V
		I _{pp} = 1 A; notes 1 and 3	–	–	11	V
	I _{pp} = 2.5 A; notes 1 and 3	–	–	15	V	
V _{BR}	breakdown voltage	I _Z = 1 mA				
	PESD3V3L2UM		5.32	5.6	5.88	V
	PESD5V0L2UM		6.46	6.8	7.14	V
S _Z	temperature coefficient	I _Z = 1 mA				
	PESD3V3L2UM		–	1.3	–	mV/K
	PESD5V0L2UM		–	2.9	–	mV/K
r _{diff}	differential resistance	I _R = 1 mA				
	PESD3V3L2UM		–	–	200	Ω
	PESD5V0L2UM		–	–	100	Ω
C _d	diode capacitance PESD3V3L2UM	f = 1 MHz; V _R = 0	–	22	28	pF
		f = 1 MHz; V _R = 5	–	12	17	pF
	PESD5V0L2UM	f = 1 MHz; V _R = 0	–	16	19	pF
		f = 1 MHz; V _R = 5	–	8	11	pF

Notes

1. Non-repetitive current pulse 8/20 μs exponential decay waveform; see Fig.5.
2. Pins 1 and 3 or 2 and 3.
3. Pins 1 and 2.

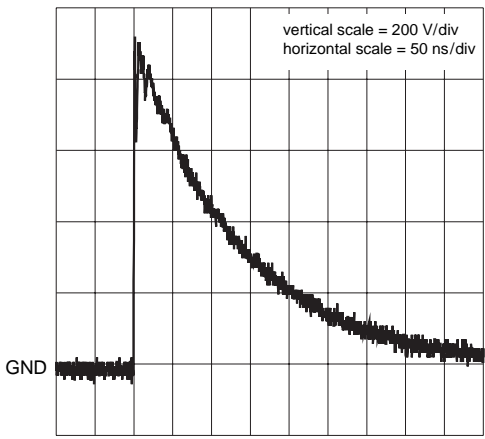
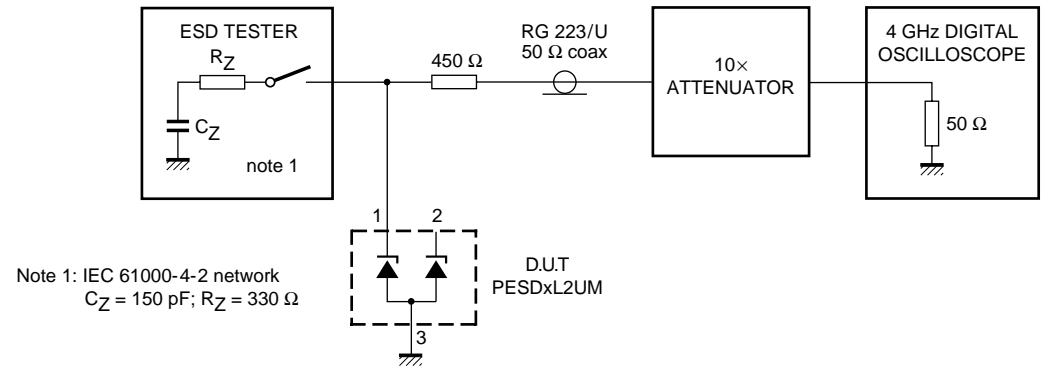
Low capacitance double ESD protection diode

PESDxL2UM series

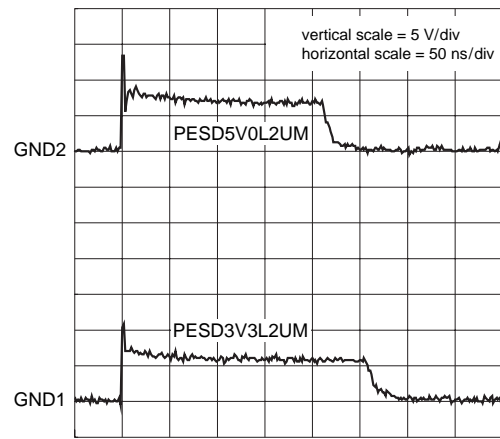


Low capacitance double ESD protection diode

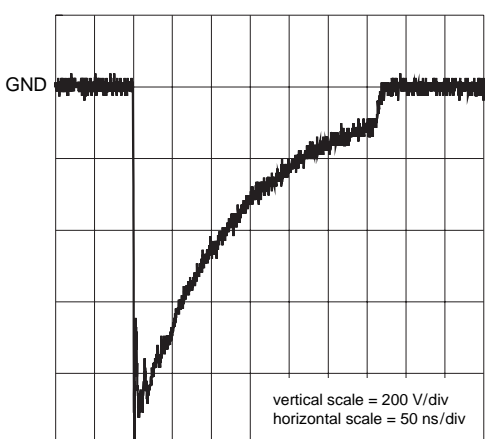
PESDxL2UM series



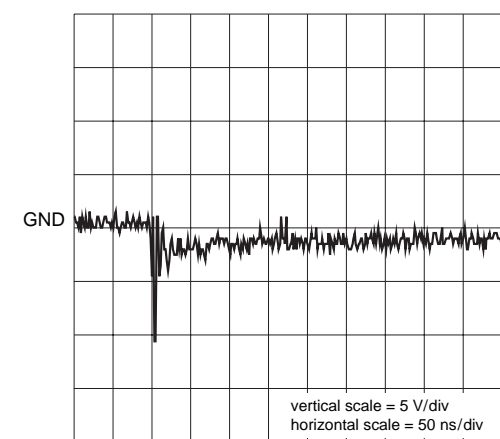
unclamped +1 kV ESD voltage waveform
(IEC 61000-4-2 network)



clamped +1 kV ESD voltage waveform
(IEC 61000-4-2 network)



unclamped -1 kV ESD voltage waveform
(IEC 61000-4-2 network)



clamped -1 kV ESD voltage waveform
(IEC 61000-4-2 network)

MLE219

Fig.6 ESD clamping test set-up and waveforms.

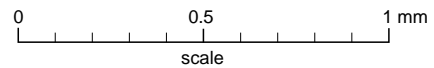
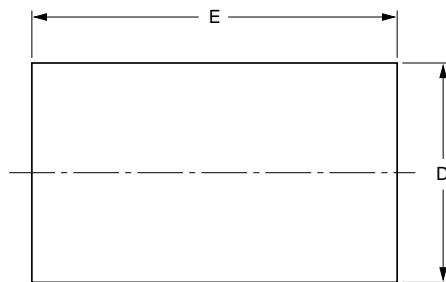
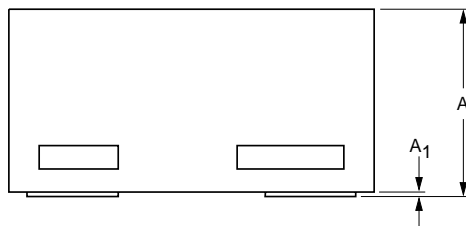
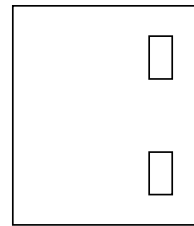
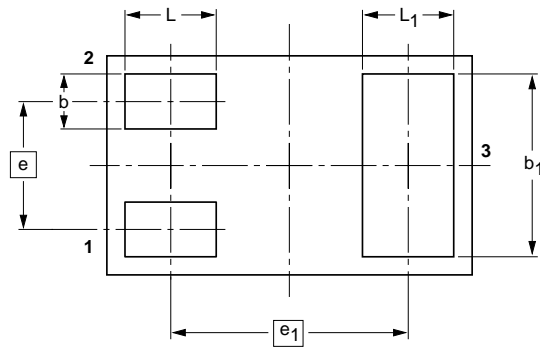
Low capacitance double ESD protection diode

PESDxL2UM series

PACKAGE OUTLINE

Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883



DIMENSIONS (mm are the original dimensions)

UNIT	A ⁽¹⁾	A ₁ max.	b	b ₁	D	E	e	e ₁	L	L ₁
mm	0.50 0.46	0.03	0.20 0.12	0.55 0.47	0.62 0.55	1.02 0.95	0.35	0.65	0.30 0.22	0.30 0.22

Note

1. Including plating thickness

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT883			SC-101		03-02-05 03-04-03

Low capacitance double ESD protection diode

PESDxL2UM series

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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